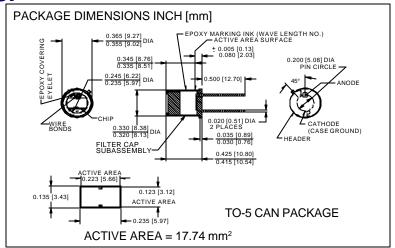
PHOTONIC Silicon Photodiode, Filter Combination Photovoltaic **DETECTORS INC.** 550 nm (green color) Type PDV-V404





FEATURES

- 550 nm CWL
- 70 nm FWHM
- · Large active area

DESCRIPTION: The **PDV-V404** is a silicon,

PIN planar diffused, photodiode with a green color 550 nm */-2 nm CWL wide band interferance filter and a wide 70 nm half bandwidth. Ideal for photometry & radiometry measurment applications.

APPLICATIONS

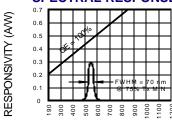
- Green color matching
- Color meters
- Film processing

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
V _{BR}	Reverse Voltage		100	V	
T _{STG}	Storage Temperature -20		+85	°C	
То	Operating Temperature Range	-15	+70	°С	
Ts	Soldering Temperature*		+240	°C	
I _L	Light Current		0.5	mA	

^{1/16} inch from case for 3 secs max

SPECTRAL RESPONSE



WAVELENGTH (nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

ELECTRO OF HORE OFFICE CHARACTER (174-20 O GITTER WISE HORS)									
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS			
lsc	Short Circuit Current***	H = 100 fc, 2850 K	150	200		μA			
ΙD	Dark Current	$H = 0$, $V_R = 10 \text{ mV}$		10	50	pА			
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	.20	2		GΩ			
TC Rsh	Rsн Temp. Coefficient	H = 0, V _R = 10 mV		-8		%/℃			
Cı	Junction Capacitance	H = 0, V _R = 10 V**		1700		pF			
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		550		nm			
HBW	Half Bandwidth	(FWHM)		70		nm			
V _{BR}	Breakdown Voltage	I = 10 μιΑ	50	75		V			
N EP	Noise Equivalent Power	V _R = 10 mV @ Peak		9x10 ⁻¹⁵		W/ √ Hz			
tr	Response Time	RL = 1 KΩ V _R = 10 V		1.0		μS			

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f = 1 MHz, ***without filter [FORM NO. 100-PDV-V404 REV A]